

PATENT ASSIGNMENT

Electronic Version v1.1
 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
MOSEL VITELIC INC.	01/18/2012
RECEIVING PARTY DATA	
Name:	PROMOS TECHNOLOGIES INC.
Street Address:	No. 19-1, Li Hsin Road
Internal Address:	Science-Based Industrial Park
City:	Hsinchu
State/Country:	TAIWAN
PROPERTY NUMBERS Total: 22	
Property Type	Number
Application Number:	10976620
Application Number:	09187197
Application Number:	09796166
Application Number:	10029930
Application Number:	10074859
Application Number:	10113705
Application Number:	10133087
Application Number:	10218376
Application Number:	10219092
Application Number:	10219094
Application Number:	10232260
Application Number:	10263397
Application Number:	10346513
Application Number:	09216078
Application Number:	10397478

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Application Number:	10453771
Application Number:	10652664
Application Number:	10652442
Application Number:	10668434
Application Number:	10671814
Application Number:	10677568
Application Number:	10652635

CORRESPONDENCE DATA

Fax Number: (801)212-2037

Phone: 8013283600

Email: wcress@kmclaw.com

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent via US Mail.

Correspondent Name: Evan R. Witt

Address Line 1: 60 East South Temple

Address Line 2: 1800 Eagle Gate Tower

Address Line 4: Salt Lake City, UTAH 84111

ATTORNEY DOCKET NUMBER:	15248.356
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NAME OF SUBMITTER:	Evan R. Witt
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Total Attachments: 4

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ASSIGNMENT OF APPLICATIONS/PATENTS

Whereas, MOSEL VITELIC INC., a corporation of Taiwan, R.O.C herein referred to "assignor" whose mailing address is No.1, Creation Rd.1, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C., is the owner of the entire right, title and interest in and to the inventions described in United States Patent Applications/Patents as follows:

1. Application No.: 09/187,197 Patent No.: 7,045,435
Entitled: Shallow trench isolation method for a semiconductor wafer
2. Application No.: 09/796,166 Patent No.: 6,758,940
Entitled: Apparatus and method for controlling boiling conditions of hot phosphoric acid solution with pressure adjustment
3. Application No.: 10/029,930 Patent No.: 6,696,672
Entitled: Heating lamp brackets for reaction chambers of evaporation coating machines
4. Application No.: 10/074,859 Patent No.: 6,826,822
Entitled: Method for preparing rubber plate used in an ion implanter
5. Application No.: 10/113,705 Patent No.: 6,699,789
Entitled: Metallization process to reduce stress between Al-Cu layer and titanium nitride layer
6. Application No.: 10/133,087 Patent No.: 6,680,261
Entitled: Method of reducing boron outgassing at trench power IC's oxidation process for sacrificial oxide layer
7. Application No.: 10/218,376 Patent No.: 6,756,168
Entitled: Determining exposure time of wafer photolithography process
8. Application No.: 10/219,092 Patent No.: 6,677,223
Entitled: Transistor with highly uniform threshold voltage

9. Application No.: 10/219,094 Patent No.: 6,812,148
Entitled: Preventing gate oxide thinning effect in a recess LOCOS process
10. Application No.: 10/232,260 Patent No.: 6,821,913
Entitled: Method for forming dual oxide layers at bottom of trench
11. Application No.: 10/263,397 Patent No.: 6,677,216
Entitled: Method of making IC capacitor
12. Application No.: 10/346,513 Patent No.: 6,743,075
Entitled: Method for determining chemical mechanical polishing time
13. Application No.: 09/216,078 Patent No.: 6,784,115
Entitled: Method of simultaneously implementing differential gate oxide thickness using fluorine bearing impurities
14. Application No.: 10/397,478 Patent No.: 7,046,551
Entitled: Nonvolatile memories with asymmetric transistors, nonvolatile memories with high voltage lines extending in the column direction, and nonvolatile memories with decoding circuits sharing a common area
15. Application No.: 10/453,771 Patent No.: 6,709,952
Entitled: Method of forming a bottom oxide layer in a trench
16. Application No.: 10/652,664 Patent No.: 6,880,382
Entitled: Leakage detecting method for use in oxidizing system of forming oxide layer
17. Application No.: 10/652,442 Patent No.: 6,855,986
Entitled: Termination structure for trench DMOS device and method of making the same
18. Application No.: 10/668,434 Patent No.: 6,888,197
Entitled: Power metal oxide semiconductor field effect transistor layout

19. Application No.: 10/671,814 Patent No.: 7,047,620
Entitled: Method for assembling a scrubber
20. Application No.: 10/677,568 Patent No.: 6,974,749
Entitled: Bottom oxide formation process for preventing formation of voids in trench
21. Application No.: 10/652,635 Patent No.: 6,828,196
Entitled: Trench filling process for preventing formation of voids in trench
22. Application No.: 10/771,957 Patent No.: 7,087,958
Entitled: Termination structure of DMOS device
23. Application No.: 10/942,381 Patent No.: 7,192,789
Entitled: Method for monitoring an ion implanter
24. Application No.: 10/771,808 Patent No.: 6,989,306
Entitled: Termination structure of DMOS device and method of forming the same
25. Application No.: 10/771,688 Patent No.: 6,991,994
Entitled: Method of forming rounded corner in trench
26. Application No.: 10/774,212 Patent No.: 7,084,457
Entitled: DMOS device having a trenched bus structure
27. Application No.: 10/817,567 Patent No.: 6,916,126
Entitled: Developing method for semiconductor substrate
28. Application No.: 11/056,450 Patent No.: 6,998,315
Entitled: Termination structure for trench DMOS device and method of making the same
29. Application No.: 11/329,870 Patent No.: 7,265,024
Entitled: DMOS device having a trenched bus structure

30. Application No.: 10/976,620

Filing Date: 10-29-2004

Entitled: Rubber plate used in an ion implanter and method of preparing the same

Whereas, PROMOS TECHNOLOGIES INC., a corporation of Taiwan, R.O.C herein referred to "assignee" whose mailing address is No.19-1, Li Hsin Road, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C., is desirous of acquiring the entire right, title and interest in the same;

Now, therefore, the Assignor transfers the hereinbefore patents are accordance with Assignment Agreement entered into on 12, 23, 2003, between MOSEL VITELIC INC. and PROMOS TECHNOLOGIES INC, all rights and obligations in whole or in part are accordance with the Assignment Agreement as well.

Executed this 18th day of January, 2012, at Hsinchu, Taiwan.
(city, state)

MOSEL VITELIC INC
Assignor


Name: REBECCA TANG
Title: Authorized Representative